

ABSTRACT

Disclosed is a method for forming a shallow trench. The method of the present invention
5 comprises steps of providing a substrate; forming a plurality of operation layers on the
substrate; forming photoresist on the uppermost one of the operation layers to define a
position to be etched; etching a portion of the operation layers at said position to form an
opening; forming a spacing layer on the sidewall of the opening; and etching a portion of the
substrate corresponding to the opening to form a shallow trench. By the etching method of the
10 present invention, a striation phenomenon caused by the common mask etch is avoided.